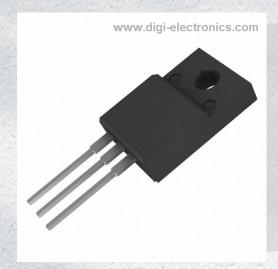


# FJAF6916TU Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number FJAF6916TU-DG

Manufacturer onsemi

Manufacturer Product Number FJAF6916TU

Description TRANS NPN 800V 16A TO3PF

Detailed Description Bipolar (BJT) Transistor NPN 800 V 16 A 60 W Throu

gh Hole TO-3PF



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
FJAF6916TU	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	16 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, Ic:
800 V	3V @ 2.5A, 10A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
1mA	6 @ 8.5A, 5V
Power - Max:	Frequency - Transition:
60 W	
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-3P-3 Full Pack	TO-3PF
Base Product Number:	
FJAF6916	

# **Environmental & Export classification**

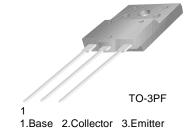
Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541 29 0095



### **FJAF6916**

### **High Voltage Color Display Horizontal Deflection Output**

- High Collector-Base Breakdown Voltage : BV<sub>CBO</sub> = 1700V
  Low Saturation Voltage : V<sub>CE</sub>(sat) = 3V (Max.)
- For Color Monitor



## **NPN Triple Diffused Planar Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>CBO</sub>	Collector-Base Voltage	1700	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current (DC)	16	Α
I <sub>CP</sub> *	Collector Current (Pulse)	30	Α
P <sub>C</sub>	Collector Dissipation	60	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> Pulse Test: PW=300µs, duty Cycle=2% Pulsed

# Electrical Characteristics $\ensuremath{\mathsf{T}}_C = 25\ensuremath{\,^{\circ}}\ensuremath{\mathsf{C}}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
I <sub>CES</sub>	Collector Cut-off Current	V <sub>CB</sub> =1400V, R <sub>BE</sub> =0			1	mA
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =800V, I <sub>E</sub> =0			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =4V, I <sub>C</sub> =0			1	mA
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =500μA, I <sub>E</sub> =0	1700			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =5mA, I <sub>B</sub> =0	800			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =500μA, I <sub>C</sub> =0	6			V
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	10			
h <sub>FE2</sub>		$V_{CE}$ =5V, $I_{C}$ =8.5A	6		9	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10A, I <sub>B</sub> =2.5A			3	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =10A, I <sub>B</sub> =2.5A			1.5	V
t <sub>STG</sub> *	Storage Time	$V_{CC}$ =200V, $I_{C}$ =8A, $R_{L}$ =25 $\Omega$			4	μs
t <sub>F</sub> *	Fall Time	I <sub>B1</sub> =1.6A, I <sub>B2</sub> =-3.2A			0.3	μs

<sup>\*</sup> Pulse Test: PW=20µs, duty Cycle=1% Pulsed

### Thermal Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Тур	Max	Units
$R_{\theta iC}$	Thermal Resistance, Junction to Case		2.08	°C/W

# **Typical Characteristics**

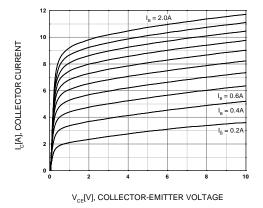


Figure 1. Static Characteristics

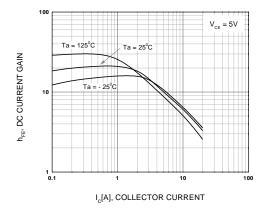


Figure 2. DC Current Gain

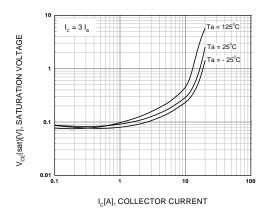


Figure 3. Collector-Emitter Saturation Voltage

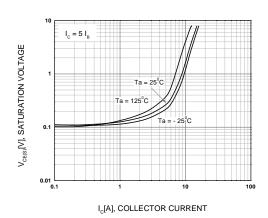


Figure 4. Collector-Emitter Saturation Voltage

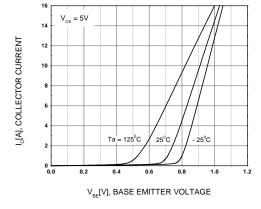


Figure 5. Base-Emitter On Voltage

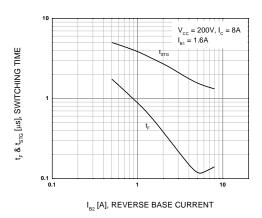


Figure 6. Resistive Load Switching Time

©2001 Fairchild Semiconductor Corporation



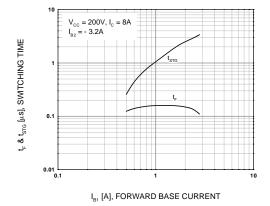


Figure 7. Resistive Load Switching Time

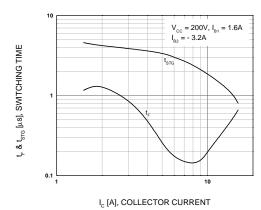


Figure 8. Resistive Load Switching Time

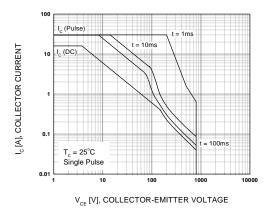


Figure 9. Forward Bias Safe Operating Area

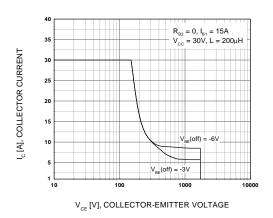


Figure 10. Reverse Bias Safe Operating Area

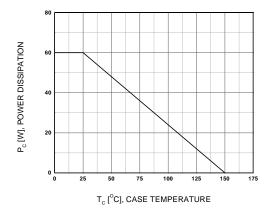
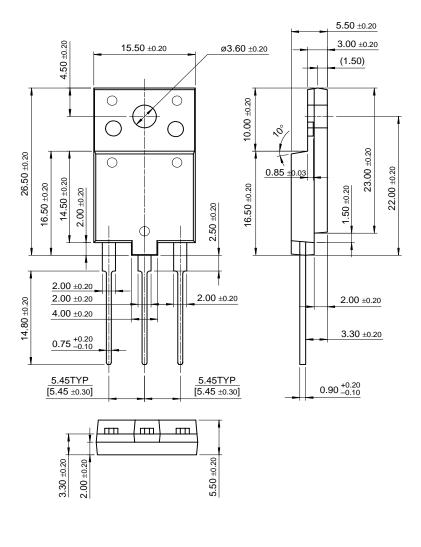


Figure 11. Power Derating

# **Package Demensions**

# TO-3PF



#### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

FAST® ACEx™ OPTOLOGIC™ SMART START™ Bottomless™  $FASTr^{TM}$ OPTOPLANAR™ STAR\*POWER™ CoolFET™  $\mathsf{FRFET}^\mathsf{TM}$  $PACMAN^{TM}$ Stealth™  $CROSSVOLT^{\intercal M}$ GlobalOptoisolator™ РОРТМ SuperSOT™-3 DenseTrench™ GTO™ Power247™ SuperSOT™-6  $\mathsf{PowerTrench}^{\mathbb{R}}$ **DOME™** HiSeC™ SuperSOT™-8 EcoSPARK™ ISOPLANAR™ QFET™ SyncFET™  $E^2CMOS^{TM}$ QSTM LittleFET™ TruTranslation™ EnSigna™ MicroFET™ QT Optoelectronics™ TinyLogic™ FACT™  $MicroPak^{TM}$ UHC™ Quiet Series™ SLIENT SWITCHER®  $\mathsf{UltraFET}^{\mathbb{R}}$ FACT Quiet Series™ MICROWIRE™

STAR\*POWER is used under license

#### **DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

 $VCX^{TM}$ 



### **OUR CERTIFICATE**

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com

















Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com